NSN 5962-01-444-9516

Memory Microcircuit - Page 1 of 1



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Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+135.0 degrees celsius
End Application:
F-15i
Features Provided:
Electrostatic sensitive and monolithic and synchronous and parallel operation
Inclosure Material:
Silicon
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Criticality Code Justification:
Cbbl
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, memory, cmos, 1k x 8 parallel synchronous fifo, monolithic silicon
Voltage Rating And Type Per Characteristic:
-0.5 volts total supply and 7.0 volts total supply
Time Rating Per Chacteristic:
25.00 nanoseconds af output megawatts
Memory Device Type:
First-in first-out
Special Features:
Descriptive designator cdip3-t28 or gdip4-t28
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
28 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:

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